# **Precision Continuum Receivers for Astrophysical Applications**

Edward J. Wollack NASA Goddard Space Flight Center Greenbelt MD, 20771

RadioNet FP7 "Receiver Gain Stability" Workshop Cagliari, Sardinian, Italy

~300K

~80K

~20K

~3K

# Low-Noise HFET Applications...

- Communications:
  - Direct Broadcast Satellite...
  - Receiver IF Backend...
  - Secure Communication Links...
- Instrumentation:
- Imaging and Detection:
  - Remote Sensing…
  - Contraband Detection...
  - Collision Avoidance Radar...
  - Smart Munition Sensors...
- Thermal Electrically Cooled Satellite Ground Stations
- Passively Cooled Satellite Receivers

#### Actively Cooled Receiver Systems

- Deep Space Network Receivers...
- Radio Astronomy...
  - Low-Noise Broad-Band Radiometers...
  - Low-Noise Receiver Frontends...
  - Low-Noise Receiver Backends...

#### • Low-Noise Detector Applications

- Direct Power Detection, Heterodyne Front-Ends, SIS Mixer IF amplifier...
- Kinetic Inductance Bolometic Readout...
- Low-Noise Electrometer Readout, Johnson Noise Thermometry...
- Particle Accelerator Beam Monitor (Stochastic Cooling)...
- Gravitational Wave and Axion Detector Readouts...

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Require Knowledge of Performance...

- Average: Noise, Gain, Phase
- Variation/Sensitivity: Amplitude, Phase

- Thermal Electrically Cooled Satellite Ground Stations
- Passively Cooled Satellite Receivers
- Actively Cooled Receiver Systems
  - Deep Space Network Receivers...
  - Radio Astronomy...
    - Low-Noise Broad-Band Radiometers...
    - Low-Noise Receiver Frontends...
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#### Low-Noise Detector Applications

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# **Device Stability:** '1/f' - Noise

- Device Configuration and Material Contributions:
  - Trap Density and Location...
  - Surface Passivation, Interface Quality, Material Stability...
  - Device Environmental Bias Sensitivities...
    - Gate/Drain/Source Relative Electrical Bias
    - Thermal, Ambient Magnetic Field...
    - Electromagnetic/Particle/Radiation Exposure...
    - Package Environment and Integrity...
- Receiver Design Considerations:
  - Topology/Configuration (e.g. correlation vs. total power)
  - RF Bandwidth, Modulation Rate, Radiometric Offset...
  - Scan and Calibration Rates, Observation Interconnectivity...
- Mathematically: Sensor has Memory or Feedback
  - "Popcorn" or distribution of time scales  $\rightarrow 1/f$  but time domain differ
  - Intrinsic device 1/f can easily be masked by other issues...
  - Lack of a well defined mean value challenge for end user...

...given the *intrinsic* detector's behavior our goal is provide a suitable environment and receiver architecture which achieves near optimal radiometric imaging performance...





FIG. 3.—Typical power spectra,  $S_v$ , of the receiver output. The data were taken while observing the sky during good weather. For SK95Q, the two-point and three-point offsets (see §§ 4.1 and 5) are manifest as the spectral features at 3 and 6 Hz ( $\zeta < 1.5 \text{ mK s}^{1/2} \text{ deg}^{-1}$ ). For SK94K<sub>a</sub>, only the two-point offset at 4 Hz is evident ( $\zeta < 0.9 \text{ mK s}^{1/2} \text{ deg}^{-1}$ ). Data taken under laboratory conditions have an indistinguishable 1/f component that originates from the cooled HEMTs. Given the approximately equal bandwidths in the K<sub>a</sub> and Q systems, the higher Q-band 1/f knee reflects a lower gain stability. At  $f \ge 100$  Hz the power spectra for both radiometers agree with the sensitivity derived from the measured RF bandwidth and system temperature. At 8 Hz, these results may be compared to  $S_{sky}$  in Table 3. The slight differences between the plot and the table result from the atmospheric noise contribution.

Wollack, E.J., et al, "An Instrument for Investigation of the Cosmic Microwave Background Radiation at Intermediate Angular Scales", 1997 ApJ, 476





FIG. 2. The measured spectral density of NRAO amplifier B11 at physical temperature,  $T_{amb}$ =18 K. The data are normalized to the spectral density at 5 kHz. Filled and unfilled symbols indicate measurements taken with the amplifier's light-emitting diode respectively in the off and on states. No measurable difference in the rf noise or gain was noted upon energizing the LEDs. The best fit spectral index of the  $1/f^{\alpha}$  component of the recorded data is  $\alpha$ =0.9±0.1. Within the measurement errors  $\alpha$  is independent of LED illumination status. The best fit magnitude of the 1/f component of the noise spectrum was noted to increase by ~35% upon illuminating the amplifier HEMTs with the LED lamps.

FIG. 3. The variation in the amplifier gain spectral density at physical temperature  $T_{\rm amb}$ =18 K as a function of source-drain current. In this test, all five stages of amplifier B11 were set at  $I_{\rm ds}$  and the magnitude of the amplifier gain fluctuation spectral density was recorded. Filled and unfilled symbols indicate measurements taken with the amplifier's light emitting diode, respectively, in the off and on states. For the amplifier under test, the variation in the effective rf bandwidth was a perturbation on the change in  $\delta g_1^2$  as a function of drain current.

*Conclusion:* Device changes which lead to noise/gain improvements can potentially degrade amplifier stability – rethink architecture for broadband radiometry...

Wollack, E.J., "High-Electron-Mobility-Transistor Gain Stability and its Design Implications for Wide Band Millimeter Wave Receivers," 1995, Review of Scientific Instruments, Vol. 66(8), pp. 4305-4312.



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**Observation:** Low frequency fluctuations intrinsic to the device modulate the effective bias point and appear as upconverted gain variations in the RF output of the amplifier - the end effect is an increase in the observed noise spectra.

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Fig. 1. Simplified model of the radiometer used to explain the correlation technique.



WWW TEMPERATURE ORTHOMODE REGULATED LOAD TRANSDUCER CRYOGENIC 30dB, 30dB HEMT AMPLIFIERS 15K ş 50dB 50dB CHANNEL B CHANNEL A 32-35 GHz 32-35 GHz 26-29 GHz 29-32 GHz 29-32 GHz GHz BANDPASS 26-29 ( FILTERS SQUARE LAW DETECTORS A1 A2 A3 B3 B2 B1

Fig. 4. Spectral density of the power fluctuations obtained from the cross-correlations  $A1 \times A2$  (dashed) and  $A1 \times B1$  (solid) with the radiometer configured as in Fig. 2.



Jarosik, N., et al., "Measurements of the Low Frequency Noise Properties of a 30 GHz High-Electron-Mobility-Transistor Amplifier," June 1993, Princeton University Physics, Technical Report.

Jarosik, N. "Measurements of the low-frequency-gain fluctuations of a 30-GHz high-electron-mobility-transistor cryogenic amplifier", 1996, IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 2, pp. 193-197.



Fig. 7. Spectral density of the power fluctuations obtained from the cross-correlation between different frequency bands of the two radiometer channels,  $A3 \times B2$  and  $A2 \times B1$ .



Fig. 9. Cross-correlations between the output power of radiometer channel A1 and the drain current of the input transistor of the HEMT amplifier  $(A1 \times I_{d1})$  and the drain current of the final transistor of the HEMT amplifier  $(A1 \times I_{d4})$ .

$$D_{\delta g \, i_d} = \frac{\left\langle \delta g \cdot \delta i_d \right\rangle}{\sqrt{\left\langle \delta g^2 \right\rangle \left\langle \delta i_d^2 \right\rangle}} \sim 0.3$$



Fig. 5. The radiometer as configured to measure the HEMT amplifier's characteristics.

Jarosik, N. "Measurements of the low-frequency-gain fluctuations of a 30-GHz high-electron-mobility-transistor cryogenic amplifier", 1996, IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 2, pp. 193-197.



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*Observation:* Low frequency amplifier response is dominated by gain-like variations having ~0.3 correlation with device drain current variation...



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Jarosik, N. "Measurements of the low-frequency-gain cryogenic amplifier", 1996, IEEE Transactions on Mi

#### Stabilization Spin-Off Ideas...

- Stabilization or "Pilot" Tone...
- Multi-Level Calibration...
- Pre-Whiten Data to Limit Noise...
- Use Measurement Transconductance or Drain Current as Proxy for Gain Variation and Correct Radiometric Data...

...all of these approaches have limitations in addressing underlying concern for precision broadband radiometry...

**Comments:** If the device conductance is varying the associated capacitances (i.e.,  $C_{ds,}$  $C_{dg,} C_{gs,...}$ ) in the region will also change. This can be seen by considering the influence of variations in the local conductivity and dielectric constant (e.g., as initiated by interaction of charges with *g*-*r* trap site) on the device's model parameters. The parameter's mean and variance need to be consistently handled in modeling the response...

### **Device Scaling Perspective...**

• HEMT Noise, Gain, and Stability are fundamentally linked:

$$T_{\min} \approx \sqrt{T_d T_g} \cdot \frac{f_{\max}}{f} \qquad G_{A_{opt}} \approx \sqrt{\frac{4T_d}{T_g}} \cdot \frac{f_{\max}}{f}$$

$$f_{\max} \sim f_T \approx \frac{v_{sat}}{2\pi l_g} \qquad \frac{\langle i_v^2 \rangle}{I^2} \sim \frac{\alpha_H}{N_c f}$$

$$S_T = T_{sys} \cdot \left[\frac{2}{\Delta v_{rf}} + \delta g^2(f) + \delta t^2(f)\right]^{1/2}$$
Gain variation increases as device gate scale reduced...
$$\delta t^2(f) << \delta g^2(f) \propto \frac{N_{stages}}{A_{gate}J_{ds}} \cdot \frac{1}{f}$$
Variation can yield inter-channel correlation...
$$\rho_{ij} = \frac{\delta g^2(f)}{2/\Delta v_{rf} + \delta g^2(f)} \Big|_{\Delta v_{rf} = 1GHz, f = 10Hz} \sim 0.3$$

Wollack, E.J., "High-Electron-Mobility-Transistor Gain Stability and its Design Implications for Wide Band Millimeter Wave Receivers," 1995, Review of Scientific Instruments, Vol. 66(8), pp. 4305-4312.

## WMAP: A Case Study...



# WMAP: Experimental Approach

- Differential radiometer design to minimize systematic errors
- 5 microwave frequencies to understand foregrounds
- 20 radiometers to allow multiple cross checks
- Sensitivity to polarization
- Accurate calibration (<0.5%)
  - ightarrow in-flight calibration using modulation of the dipole
- In-flight beam measurements on Jupiter
- Minimize sidelobes & diffracted signals from Earth, Sun, Moon  $\rightarrow$  L2 orbit
- Multiple modulation periods to identify systematic effects
- Minimize all observatory changes

 $\rightarrow$  L2 orbit; constant survey mode operations

- Thermal stability / Passive thermal control  $\rightarrow$  L2
- Rapid and complex sky scan
   →observe 30% of the sky in an hour



#### SPIN-SYNCHRONOUS NON-SKY SIGNALS WERE THE LEADING CONCERN

## WMAP Scan Strategy



## WMAP: HEMT-Based Differential Receivers



#### **WMAP: Pseudo-Correlation Radiometer**



#### **WMAP: Pseudo-Correlation Radiometer**



Jarosik, N., et al., "Design, Implementation, and Testing of the Microwave Anisotropy Probe MAP Radiometer", ApJS 145:413-436, 2003

## **WMAP: W-Band Amplifier**



## NRAO: Noise/Gain Measurement Dewar



#### **WMAP: W-Band Amplifier Gain**



Pospieszalski, M.W., et al., "Design and Performance of Wideband, Low-Noise, Millimeter-Wave Amplifiers for Microwave Anisotropy Probe Radiometers," 2000, IEEE MTT-S International Microwave Symposium Digest, Boston, MA, pp. 25-28.

### **WMAP: W-Band Amplifier Phase Tracking**



### **WMAP: Amplifier Noise Temperature**



## NRAO: Low Frequency Stability Test



### **WMAP: Amplifier Stability Test and Scaling**



Wollack, E.J. and Pospieszalski, M.W., "Characteristics of Broad-Band InP Millimeter-Wave Amplifiers for Radiometry," 1998, IEEE MTT-S International Microwave Symposium Digest, Baltimore, MD, pp. 669-672.

### WMAP: Amplifier Stability Test and Scaling





Fig. 4. Required switch frequency as a function of radiometer offset. The measured spectral index and density of gain fluctuations are used to estimate the switching frequency required to limit the noise contribution due to variations in the radiometer gain to 10% of the system noise. The filled dots indicate the switch frequency for a differencing or subtraction-type radiometer. The solid lines indicate the calibration rate required in a correlation or multiplication-type receiver as a function of the deviation from a balanced output.

### Interlude – A Tale of Two Receivers:

Instrument Architecture and Device Stability...



Beam Switched Total Power Receiver..

#### Interlude – A Tale of Two Receivers:

Instrument Architecture and Device Stability...



Bishop, C., et al., "New Measurements of Fine-Scale CMB Polarization Power Spectra from CAPMAP at both 40 and 90 GHz", ApJ 684:771Y789, 2008



Barkats, D., et al., "Cosmic Microwave Background Polarimetry Using Correlation Receivers with the PIQUE and CAPMAP Experiments", ApJS 159:1-26, 2005

# **WMAP: Instrument Integration and Test**



#### WMAP: Amplifier Life Test and Burn-In



Limon, M., et al., "Seven-Year Wilkinson Microwave Anisotropy Probe (WMAP) Observations: Explanatory Supplement," 2010, Version 4.0, http://lambda.gsfc.nasa.gov, pp. 1-190.

#### WMAP: Amplifier Life Test and Burn-In



Limon, M., et al., "Seven-Year Wilkinson Microwave Anisotropy Probe (WMAP) Observations: Explanatory Supplement," 2010, Version 4.0, http://lambda.gsfc.nasa.gov, pp. 1-190.



FIG. 2.—Noise power spectral density of the V12 radiometer obtained from 3 days of on-orbit data. Sky signals arising from the dipole, CMB, Galaxy, and point sources have been removed. The inset contains an expanded view of the low-frequency region of the same data. The flat spectrum down to very low frequencies ( $f_{\text{knee}} = 1.41 \text{ mHz}$ ) indicates proper radiometer performance.

Jarosik, N., et al., "First Year Wilkinson Microwave Anisotropy Probe (WMAP), Observations On-Orbit Radiometer Characterization, ApJS 2003, 148, 29-37.



FIG. 3.—Dependence of  $f_{\text{knee}}$  on  $T_{\text{off}}$  for the 20 radiometers comprising *WMAP*. The solid line is a power-law fit to the data of the form  $f_{\text{knee}} \propto [(|T_{\text{off}}|\Delta \nu_{\text{eff}}^{1/2})/T_{\text{sys}}]^{2/\alpha}$  with  $\alpha = 1.70$ . The scaling of  $f_{\text{knee}}$  with  $T_{\text{off}}$  indicates that  $f_{\text{knee}}$  is largely determined by radiometer gain fluctuations modulating the signal from the radiometer offsets, as expected.

Jarosik, N., et al., "First Year Wilkinson Microwave Anisotropy Probe (WMAP), Observations On-Orbit Radiometer Characterization, ApJS 2003, 148, 29-37.



FIG. 6.—Distribution of the prewhitened V12 radiometer noise obtained from 10 days of observations. Sky signals arising from the dipole, CMB, and Galaxy have been removed. Data points were cut when either radiometer beam encountered a planet or a region of high Galactic emission. The line corresponds to a unit variance Gaussian distribution normalized to the observed frequency at s = 0. The two symbols denote the values obtained from the two sides of the distribution. The highly Gaussian distribution indicates that the noise variance for each pixel of the resulting sky maps should scale inversely with the number of observations of that pixel.



# WMAP: 'First Light' Image



## WMAP: Map-Making and Calibration



- Gain and baseline calibration based on known dipole modulation due to motion of WMAP around the Sun

- COBE dipole provides shortterm transfer standard



The degree of *interconnection* in the map and *stability* over the calibration time scale is a key to controlling the introduction of strips or other artifacts in the map...

## WMAP: Improved Gain Model



## WMAP: 5-year Temperature Maps





## WMAP: ILC - 3-Color Maps

![](_page_38_Picture_1.jpeg)

## WMAP: ILC - CMB Temperature Anisotropy

![](_page_39_Figure_1.jpeg)

Consistent with a gaussian distribution and random phase...

#### **NRAO: GBT Dual-Polarization Multi-Beam Receiver**

![](_page_40_Figure_1.jpeg)

#### Selected References – Noise, '1/f', and Related Physical Processes

- M. W. Pospieszalski, "Modeling of Noise Parameters of MESFET's and MODFET's and Their Frequency and Temperature Dependence," 1989, IEEE Trans. Microwave Theory and Tech., Vol. MTT-37, pp. 1340-1350.
- M. W. Pospieszalski, et al., "Millimeter-Wave, Cryogenically-Coolable Amplifiers Using AlInAs/ GaInAs/InP HEMTs", 1993, IEEE MTT-S Digest, pp. 515-518. (HEMT leakage current noise)
- B. Hughes, "A Temperature Noise Model for Extrinsic FET's," 1992, IEEE Trans. Microwave Theory Tech., vol. 40, pp. 1821–1831.
- R.F. Voss and J. Clarke, "Flicker (1/f) Noise: Equilibrium Temperature and Resistance Fluctuations", 1976, Physical Review B, Vol. 13, No. 2, pp. 556-573. (1/f in metal films)
- M.S. Keshner, "*1/f* Noise", 1982, Proc. IEEE, Vol. 70, No. 3, pp. 212-218. (Physically insightful)
- A. van der Ziel, "Noise in Solid State Devices and Circuits", 1986, Wiley, New York. (1/f survey)
- K. Kandiah, M.O. Deighton, F.B. Whiting, "A Physical Model for Random Telegraph Signal Current in Semiconductor Devices", 1989, J. Appl. Phys., Vol. 66, No. 2, pp. 937-948.
- G. Reimbold, "Modified 1/f Trapping Noise Theory and Experiments in MOS Transistors Biased from Weak to Strong Inversion – Influence of Interface States", 1984, IEEE Transactions on Electron Devices, Vol. ED-31, No. 9, pp. 1190 – 1198.
- J.-M Peransin, et al., "1/f Noise in MODFET's at Low Drain Bias", 1990, IEEE Transactions on Electron Devices, Vol. 37, No. 10, pp. 2250-2253.
- A. Longoni, E. Gatti, R. Sacco, "Trapping Noise in Semiconductor Devices: A Method for Determining the Noise Spectrum as a Function of the Trap Position," 1995, J. Appl. Phys., Vol. 78, No. 10, pp. 6283-6297.
- H.C. Duran, et al., "Low-Frequency Noise Properties of Selectively Dry Etched InP HEMT", 1998, IEEE Transactions on Electron Devices, Vol. 45, No. 6, pp. 1219-1225.

#### **Selected References – Receivers, Radiometers, and Stability**

- R. Dicke, "The Measurement of Thermal Radiation at Microwave Frequencies," 1946, Rev. Sci. Instrum., Vol. 17, No. 7, pp. 268-275.
- R. Hanbury-Brown, R.Q. Twiss, "A New Type of Interferometer for Use in Radio Astronomy," 1954, Philosophical Mag., Vol. 45, No. 366, pp. 663-682.
- E.J. Blum, "Sensitivity of Correlation Radio Telescopes and Receivers," 1959, Annales, D' Astrophysique, Vol. 22, No. 2, p. 140.
- S. Weinreb, "Digital Radiometer," 1961, Proc. IRE, Vol. 49, p. 1099..
- J. Hach, "Proposal for a Continuously Calibrated Radiometer," 1966, Proc. IEEE, Vol. 54, pp. 2015-2016.
- G. Aitken, "The Multi-Correlation Receiver," 1966, Proc. IEEE (Letters), Vol. 54, pp. 703—704;
   G. Aitken, "A New Correlation Radiometer," 1968, IEEE Trans. Antennas and Propagation, Vol. 16, No. 2, pp. 224-228.
- J. Faris, "Sensitivity of a Correlation Radiometer," 1967, J. Res. Nat. Bur. Stand., Engr. & Instr., Vol. 71C, pp.153-170.
- J. Hach, "A Very Sensitive Airborne Microwave Radiometer Using Two Reference Temperatures," 1968, IEEE Transactions Microwave Theory and Techniques, Vol. 16, No. 9, pp. 629-636.
- M.S. Hersman and G.A. Poe, "Sensitivity of the Total Power Radiometer with Periodic Absolute Calibration", 1981, IEEE Trans. Microwave Theory and Techniques, Vol. 29, No. 1, pp. 32-40.
- C.R. Predmore, et al., "A Continuous Comparison Radiometer at 97GHz," 1985, IEEE Trans. on Microwave Theory and Techniques, Vol. 33, No. 1, pp. 44-51.
- S. Padin, "A Wideband Analog Continuum Correlator for Radio Astronomy," 1994, IEEE Trans. Instrum. and Measurement, Vol. 43, No. 6., pp. 782-785.

# A (Very) Brief FET History...

1930	Lilienfeld	TRANSfer-resISTOR concept proposed
		Field-Effect-Transistor (FET)
1947	Bardeen, Brattain, and Shockley	Bi-polar transistor invented
	(Bell Telephone Laboratories)	<b>B</b> i-polar-Junction-Transistor ( <b>BJT</b> )
1952	Shockley	Uni-polar transistor concept analyzed
	(Bell Telephone Laboratories)	Junction-Field-Effect-Transistor (JFET)
1966	Mead	Device structure proposed
	(California Institute of Technology)	MEtal-Semiconductor-FET (MESFET)
1967	Hooper and Lehrer	First MESFET fabricated on GaAs
	(Fairchild Semiconductor)	$(T_n \sim 450 K @ 1 GHz; T_a = 300 K)$
1970	Esaki, and Tsu (IBM)	Prediction of carrier accumulation at hetrointerface
	Loriou, Bellec, Le Rouzic	Early investigations of cooled MESFET amplifiers
	(National Telecommunications Center, France)	$(T_n \sim 120 K @ 1 GHz; T_a = 77 K)$
1975	Pucel, Haus, and Statz (Raytheon)	"PRC" FET noise model presented
1978	Dingle, Stormer, Gossard, and Wiegmann	Accumulation of carriers and increase in electron
	(AT&T Bell Laboratory)	mobility at hetrointerface demonstrated
1979	Fukui (AT&T Bell Laboratories)	Fukui scaling laws proposed for FETs
1980	Weinreb (NRAO)	Practical cryogenic FET amplifiers demonstrated
	Mimura, Hiyamizu, Fuji, and Nanbu	First hetrojunction field effect transistor reported
	(Fujitsu Laboratories, Japan)	High-Electron-Mobility-Transistor (HEMT)
	(Bell Laboratories)	Selectively-Doped-Hetrojuntion-Transistor (SDHT)
	(Thomson-CSF, France)	Two-dimensional-Electron-Gas-FET (TEGFET)
	(U of IL / Rockwell International)	MOdulation-Doped-FET (MODFET)
1982	Delagebeaudeuf and Lihn (Thomson-CSF, France)	Device design analysis presented for HFETs
1989	Pospieszalski (NRAO)	"Tg/Td" HFET noise model presented
2000	State of the Art	→ GaAs HFETs ( $T_n \sim 3K$ @ 1 GHz; $T_a = 4K$ )
	(Hughes, TRW, JPL,)	$\rightarrow$ InP HFET MMICs (>100 GHz)

### **Field Effect Transfer-Resistor:**

1,745,175

![](_page_44_Figure_1.jpeg)

J. E. LILIENFELD

Jan. 28, 1930.

![](_page_44_Figure_2.jpeg)

(a)

![](_page_44_Figure_4.jpeg)

![](_page_44_Figure_5.jpeg)

![](_page_44_Figure_6.jpeg)

(b)

Fig. 20 (a) Equivalent circuit of a MESFET and (b) physical origin of the circuit elements. (After Liechti, Ref. 8.)

### **Schockley Field Effect Transistor Model:**

![](_page_45_Figure_1.jpeg)

Shockley's model of the junction field-effect transistor. (After Dacey and Ross.